Name	NSi-01
Structure	R4 R1 
Boiling point	185℃
Vapor pressure	8.0Torr at 65℃

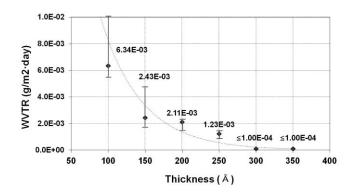


Fig. 1. The physical properties of Si precursor. Fig. 2. WVTR of the deposited SiNx film on PEN film with a varous thickness.